



Stand-off voltage: 3.3V Max
Transient protection for each line according to
IEC61000-4-2(ESD): $\pm 30\text{kV}$ (contact)
IEC61000-4-5(surge): 7A (8/20 μs)
Ultra-low capacitance: $C_J = 1.35\text{pF}$ typ.
Low leakage current: $I_R < 1\text{nA}$ typ.
Low clamping voltage: $V_{CL} = 12.0\text{V}$ typ. @ $I_{PP} = 16\text{A}$
(TLP)
Solid-state silicon technology

: SOD323

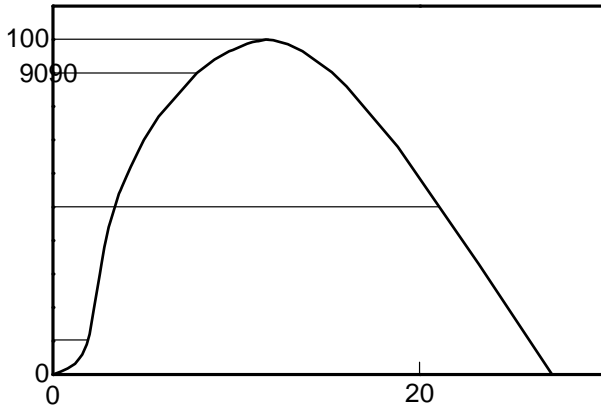
: Tin plated leads, solderable per



Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	77	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	7	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	KV
ESD according to IEC61000-4-2 contact discharge		± 30	
Junction temperature	T_J	125	$^{\circ}C$
Operating temperature	T_{OP}	-40~85	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

Reverse maximum working voltage	V_{RWM}	V				3.3
Reverse leakage current	I_R	nA	$V_{RWM} = 3.3V$		<1	50
Reverse breakdown voltage	$V_{(BR)}$	V	$I_{BR} = 1mA$	6.0	8	
Clamping voltage ¹⁾	V_{CL}	V	$I_{PP} = 16A, t_p = 100ns$		13	
Dynamic resistance ¹⁾	R_{DYN}				0.55	
Clamping voltage ²⁾	V_{CL}	V	$V_{ESD} = 8kV$		13	
Clamping voltage ³⁾	V_{CL}	V	$I_{PP} = 1A, t_p = 8/20\mu s$		8.1	9
			$I_{PP} = 7A, t_p = 8/20\mu s$		9.7	11
Junction capacitance	C_J	pF	$V_R = 0V, f = 1MHz$		0.8	1.0

8/20 μ s waveform per IEC61000 4 5



Clamping voltage vs. Peak pulse current

Contact discharge current waveform per IEC61000 4 2

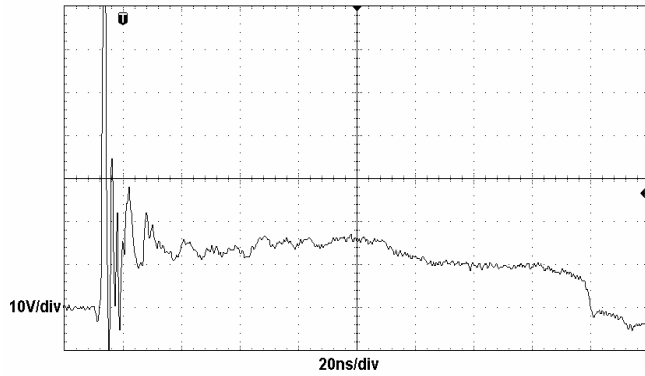
Capacitance vs. Reverse voltage

Non repetitive peak pulse power vs. Pulse time

Power derating vs. Ambient temperature



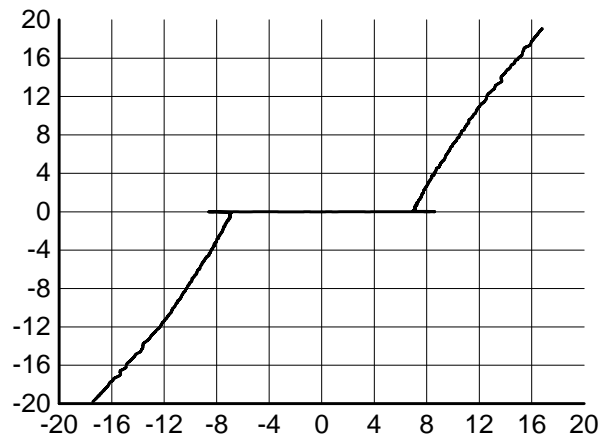
ESD clamping
(+8kV contact discharge per IEC61000 4 2)

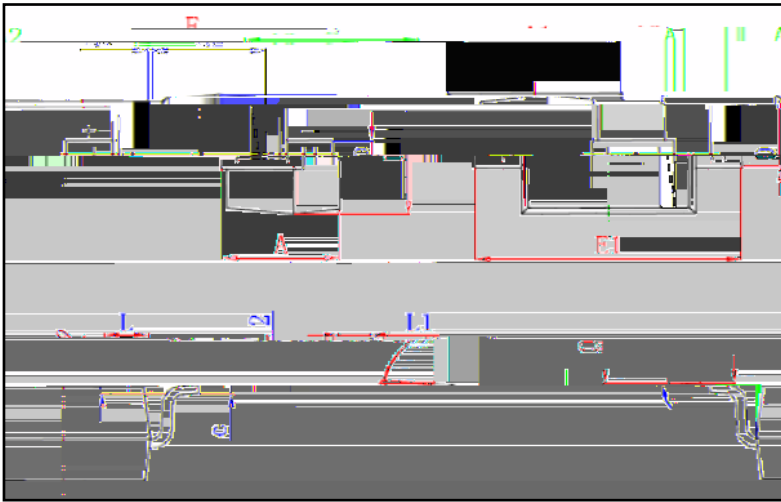


ESD clamping
(8kV contact discharge per IEC61000 4 2)

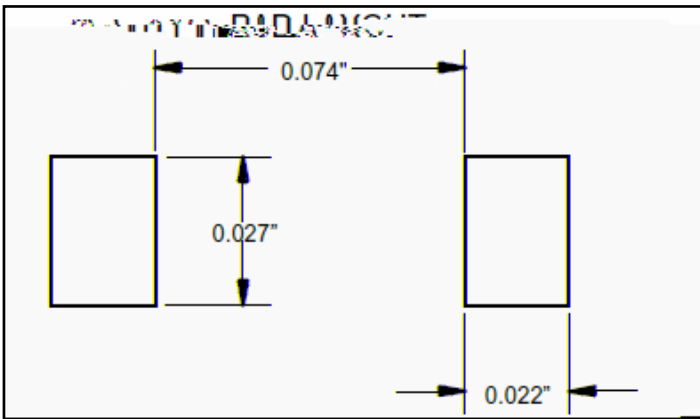


TLP Measurement





Symbol	Min	Max	Symbol	Min	Max
1.000			A		
0.100			A1	0.000	
0.900			A2	0.800	
0.400			b	0.250	
0.150				0.000	
B	1.200			1.400	
	1.2000			1.4000	
E1	2.500			2.700	
	2.5000			2.7000	
	0°			8°	



Unit inches

